

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (withdrawn) A method for producing a light emitting diode, which has a plated substrate with a mirror, comprising steps of:

- a) providing a substrate with an LED epitaxial structure including a second cladding layer, an active layer, a first cladding layer, a window and a metal contact layer sequentially formed on said substrate;
- b) etching a part of said LED epitaxial structure to expose said second cladding layer;
- c) forming a first electrode and a second electrode respectively on said metal contact layer and said exposed second cladding layer, and heating both said electrodes by rapid thermal annealing;
- d) bonding a temporary substrate to said LED epitaxial structure and said first electrode;
- e) removing said substrate provided in step a);
- f) forming a mirror beneath said LED epitaxial structure;
- g) plating a permanent substrate beneath said mirror; and
- h) removing said temporary substrate.

Claim 2 (withdrawn): The method as claimed in claim 1, wherein said substrate provided in step a) is a GaAs substrate, a sapphire substrate or an InP substrate.

- Claim 3 (withdrawn): The method as claimed in claim 1, wherein said LED epitaxial structure is made from a material selected from the group consisting of $\text{Ga}_x\text{Al}_y\text{In}_{1-x-y}\text{N}$, $(\text{Al}_x\text{Ga}_{1-x})_y\text{In}_{1-y}\text{P}$, $\text{In}_x\text{Ga}_{1-x}\text{As}$, $\text{ZnS}_x\text{Se}_{1-x}$; wherein $0 \leq x \leq 1$, $0 \leq y \leq 1$.
- Claim 4 (withdrawn): The method as claimed in claim 1, wherein said metal contact layer is partially etched to retain a portion beneath said first electrode.
- Claim 5 (withdrawn): The method as claimed in claim 1 further depositing a transparent conductive film between said first electrode and said metal contact layer.
- Claim 6 (withdrawn): The method as claimed in claim 1, wherein said temporary substrate is a glass substrate.
- Claim 7 (withdrawn): The method as claimed in claim 1, wherein said temporary substrate is bonded to said LED epitaxial structure with epoxy or wax.
- Claim 8 (withdrawn): The method as claimed in claim 1, wherein said mirror is a metal capable of forming high bandgap with said LED epitaxial structure.
- Claim 9 (withdrawn): The method as claimed in claim 8, wherein said mirror is made from a material selected from the group consisting of Ag, Pt, Pd, Au, Au/Zn, Au/Be, Au/Ge, Au/Ge/Ni, In, Sn, Al, Zn, Ge and Ni, or mixtures thereof.
- Claim 10 (withdrawn): The method as claimed in claim 1, wherein said mirror is made from a composite of a metal with a low refractivity and an insulating layer with a high refractivity, and said insulating layer is adjacent to said LED epitaxial structure.
- Claim 11 (withdrawn): The method as claimed in claim 10, wherein said composite is selected from the group consisting of Al/ Al_2O_3 ,

Al/SiO₂, Al/MgF₂, Pt/Al₂O₃, Pt/SiO₂, Pt/MgF₂, Al/Al₂O₃, Al/SiO₂,
Al/MgF₂, Au/Al₂O₃, Au/SiO₂, Au/MgF₂, Ag/Al₂O₃, Ag/SiO₂,
Ag/MgF₂.

Claim 12 (withdrawn): The method as claimed in claim 1, wherein said permanent substrate is plated beneath said mirror other than predetermined saw streets.

Claim 13 (currently amended): A light emitting diode having a plated substrate with a mirror, comprising:

an LED epitaxial structure sequentially comprising a second cladding layer, an active layer, a first cladding layer, a window and a metal contact layer, wherein said second cladding layer is partially exposed, wherein said active layer is made from a material selected from the group consisting of (Al_xGa_{1-x})_yIn_{1-y}P, Ga_xAl_yIn_{1-x-y}N, In_xGa_{1-x}As, and ZnS_xSe_{1-x}, 0 ≤ x ≤ 1, 0 ≤ y ≤ 1;

a first electrode formed on said metal contact layer;
a second electrode formed on said exposed second cladding layer;
a mirror formed beneath said LED epitaxial structure; and
a permanent metal substrate plated beneath said mirror and retaining sawing streets without plating the substrate thereon;
wherein said mirror is made from a composite, a metal or an alloy selected from the group consisting of:

Al/MgF₂, Pt/Al₂O₃, Pt/SiO₂, Pt/MgF₂, Au/SiO₂, Au/MgF₂, Ag/MgF₂;
Ag, Au, Au/Zn, Au/Be, Au/Ge, Au/Ge/Ni and Zn, or mixtures thereof
when said active layer ~~LED epitaxial structure~~ is made from
(Al_xGa_{1-x})_yIn_{1-y}P;

Ag, Pt, Pd, Al, and Ni, or mixtures thereof when said active layer
~~LED epitaxial structure~~ is made from Ga_xAl_yIn_{1-x-y}N, 0 ≤ x ≤ 1,
0 ≤ y ≤ 1;

Ag, Au, Au/Zn, Au/Be, Au/Ge, Au/Ge/Ni and Zn, or mixtures thereof
when said active layer ~~LED epitaxial structure~~ is made from

$\text{In}_x\text{Ga}_{1-x}\text{As}$, $0 \leq x \leq 1$, $0 \leq y \leq 1$; or
Ag, Pt, Pd, Au/Zn, Au/Be, Au/Ge, Au/Ge/Ni, Al and Ni, or mixtures
thereof when said active layer ~~LED epitaxial structure~~ is made
from $\text{ZnS}_x\text{Se}_{1-x}$, $0 \leq x \leq 1$, $0 \leq y \leq 1$.

Claim 14 (canceled)

Claim 15 (original): The light emitting diode as claimed in claim 13 further
comprising a transparent conductive film between said first electrode
and said metal contact layer.

Claims 16-25 (canceled)